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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

October 2013

FDP038AN06A0 / FDI038AN06A0

N-Channel PowerTrench® MOSFET

60 V, 80 A, 3.8 mΩ

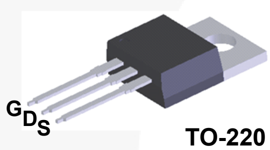
Features

- $R_{DS(on)}$ = 3.5 mΩ (Typ.) @ V_{GS} = 10 V, I_D = 80 A
- $Q_{G(tot)}$ = 96 nC (Typ.) @ V_{GS} = 10 V
- Low Miller Charge
- Low Q_{rr} Body Diode
- UIS Capability (Single Pulse and Repetitive Pulse)

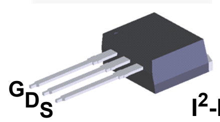
Formerly developmental type 82584

Applications

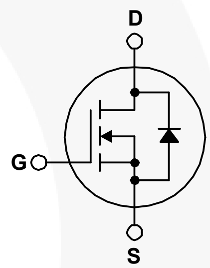
- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor drives and Uninterruptible Power Supplies



TO-220



I2-PAK



MOSFET Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	FDP038AN06A0 FDI038AN06A0	Unit
V_{DSS}	Drain to Source Voltage	60	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current Continuous (T_C < 151°C, V_{GS} = 10V)	80	A
	Continuous (T_{amb} = 25°C, V_{GS} = 10V, with $R_{\theta JA}$ = 62°C/W)	17	A
	Pulsed	Figure 4	A
E_{AS}	Single Pulse Avalanche Energy (Note 1)	625	mJ
P_D	Power dissipation	310	W
	Derate above 25°C	2.07	W/°C
T_J, T_{STG}	Operating and Storage Temperature	-55 to 175	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.48	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max. (Note 2)	62	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP038AN06A0	FDP038AN06A0	TO-220	Tube	N/A	50 units
FDI038AN06A0	FDI038AN06A0	I^2-PAK	Tube	N/A	50 units

Electrical Characteristics $T_C = 25°C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
Off Characteristics						
B_{VDSS}	Drain to Source Breakdown Voltage	$I_D = 250\mu A$, $V_{GS} = 0V$	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 50V$	-	-	1	µA
		$V_{GS} = 0V$, $T_C = 150^oC$	-	-	250	
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20V$	-	-	±100	nA
On Characteristics						
$V_{GS(TH)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\mu A$	2	-	4	V
$r_{DS(ON)}$	Drain to Source On Resistance	$I_D = 80A$, $V_{GS} = 10V$	-	0.0035	0.0038	Ω
		$I_D = 40A$, $V_{GS} = 6V$	-	0.0049	0.0074	
		$I_D = 80A$, $V_{GS} = 10V$, $T_J = 175^oC$	-	0.0071	0.0078	
Dynamic Characteristics						
C_{ISS}	Input Capacitance	$V_{DS} = 25V$, $V_{GS} = 0V$, f = 1MHz	-	6400	-	pF
C_{OSS}	Output Capacitance		-	1123	-	pF
C_{RSS}	Reverse Transfer Capacitance		-	367	-	pF
$Q_{g(TOT)}$	Total Gate Charge at 10V	$V_{GS} = 0V$ to $10V$; $V_{DD} = 30V$, $I_D = 80A$, $I_g = 1.0mA$		96	124	nC
$Q_{g(TH)}$	Threshold Gate Charge	$V_{GS} = 0V$ to $2V$	-	12	15	nC
Q_{gs}	Gate to Source Gate Charge		-	26	-	nC
Q_{gs2}	Gate Charge Threshold to Plateau		-	15	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	27	-	nC
Switching Characteristics ($V_{GS} = 10V$)						
t_{ON}	Turn-On Time	$V_{DD} = 30V$, $I_D = 80A$, $V_{GS} = 10V$, $R_{GS} = 2.4\Omega$	-	-	175	ns
$t_{d(ON)}$	Turn-On Delay Time		-	17	-	ns
t_r	Rise Time		-	144	-	ns
$t_{d(OFF)}$	Turn-Off Delay Time		-	34	-	ns
t_f	Fall Time		-	60	-	ns
t_{OFF}	Turn-Off Time		-	-	115	ns
Drain-Source Diode Characteristics						
V_{SD}	Source to Drain Diode Voltage	$I_{SD} = 80A$	-	-	1.25	V
		$I_{SD} = 40A$	-	-	1.0	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 75A$, $dI_{SD}/dt = 100A/\mu s$	-	-	38	ns
Q_{RR}	Reverse Recovered Charge	$I_{SD} = 75A$, $dI_{SD}/dt = 100A/\mu s$	-	-	39	nC

Notes:
1: Starting $T_J = 25°C$, L = 0.255mH, $I_{AS} = 70A$.
2: Pulse Width = 100s

Typical Characteristics T_C = 25°C unless otherwise noted

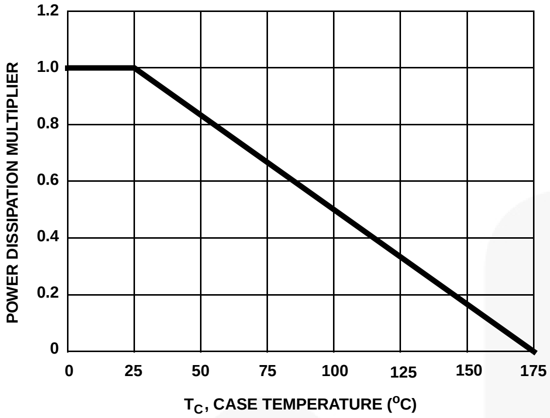


Figure 1. Normalized Power Dissipation vs Ambient Temperature

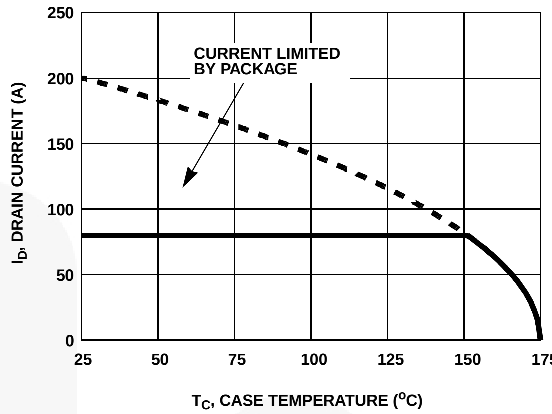


Figure 2. Maximum Continuous Drain Current vs Case Temperature

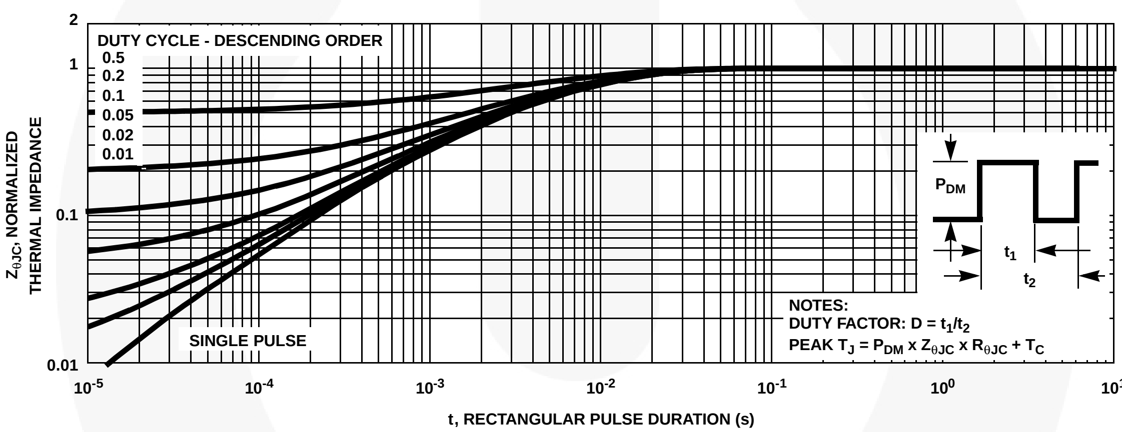


Figure 3. Normalized Maximum Transient Thermal Impedance

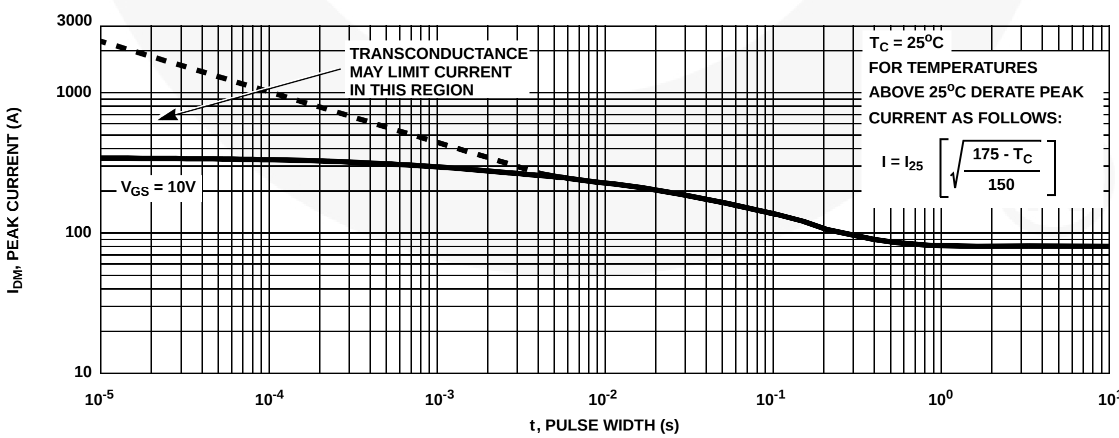


Figure 4. Peak Current Capability

Typical Characteristics T_C = 25°C unless otherwise noted

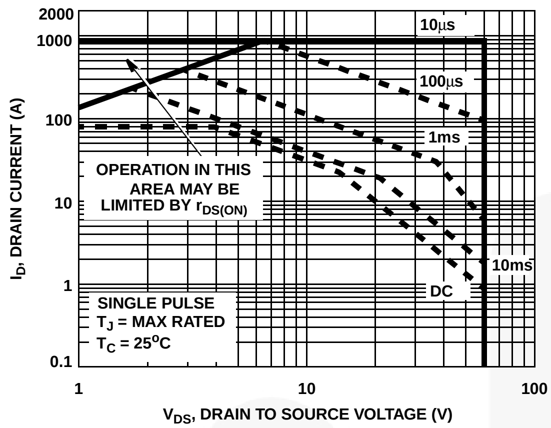
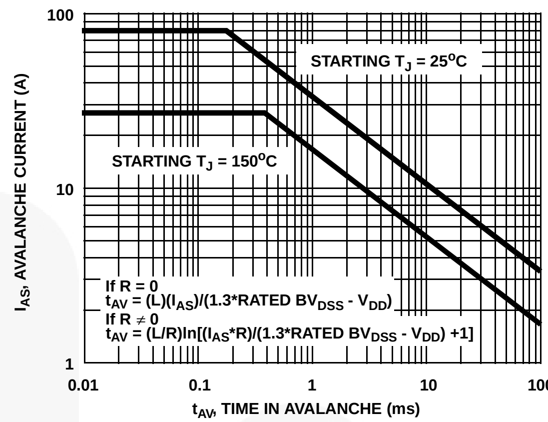


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching Capability

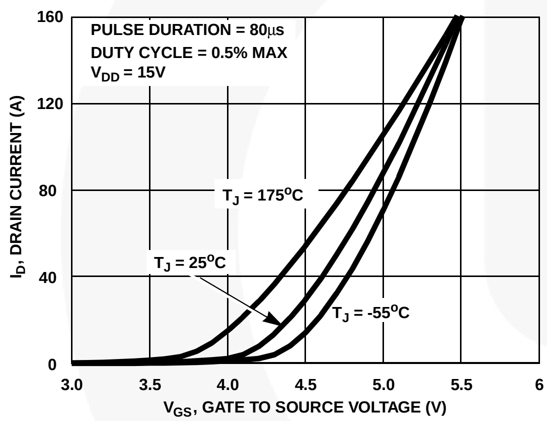


Figure 7. Transfer Characteristics

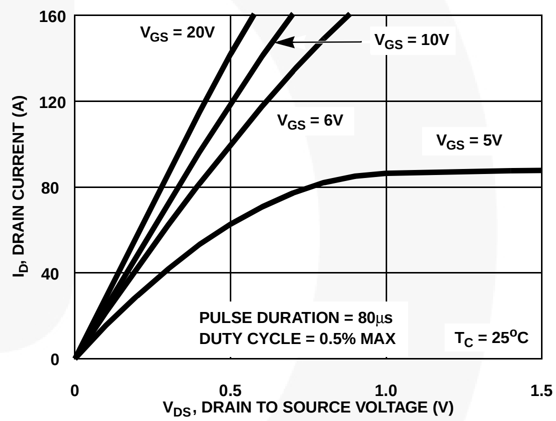


Figure 8. Saturation Characteristics

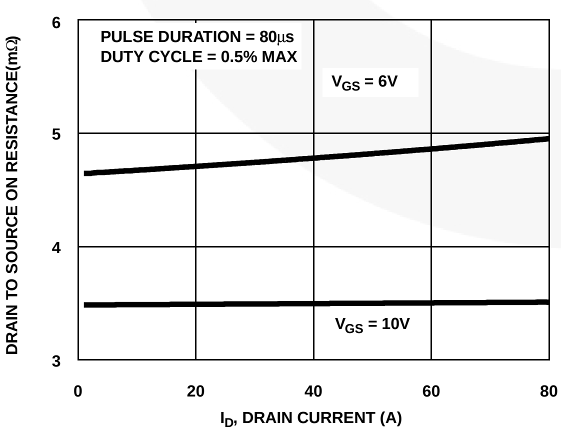


Figure 9. Drain to Source On Resistance vs Drain Current

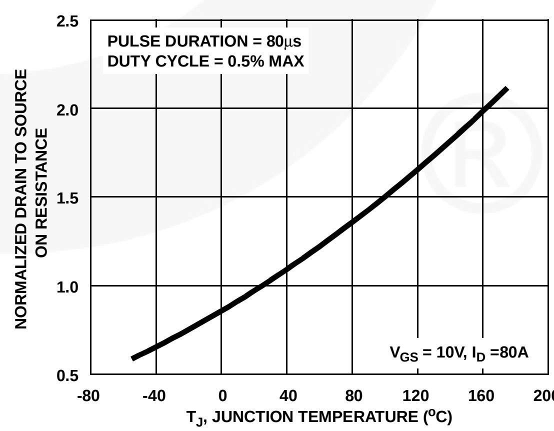


Figure 10. Normalized Drain to Source On Resistance vs Junction Temperature

Typical Characteristics T_C = 25°C unless otherwise noted

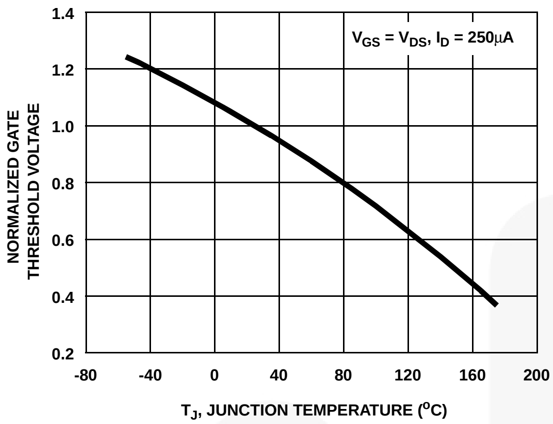


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

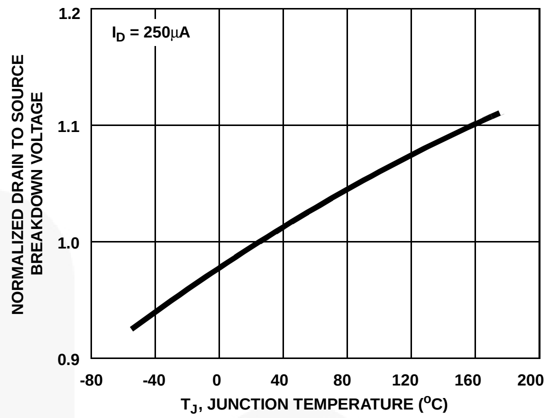


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

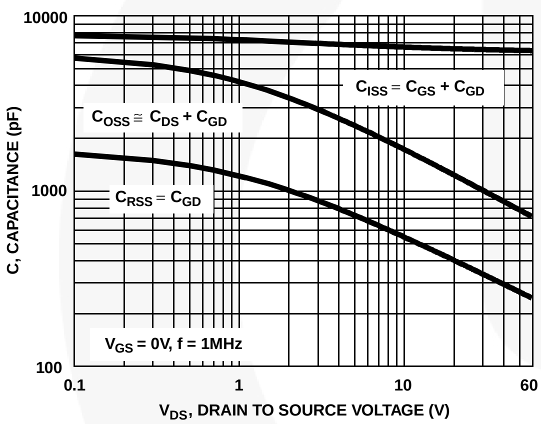


Figure 13. Capacitance vs Drain to Source Voltage

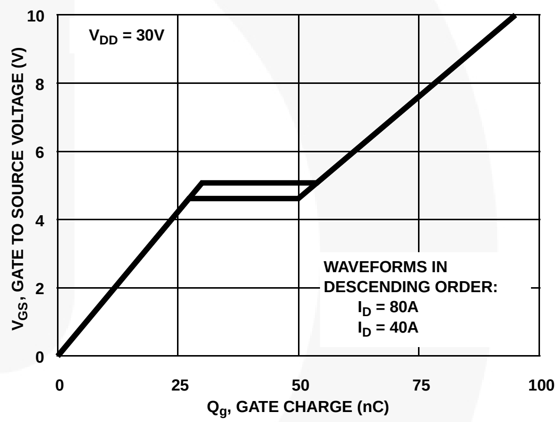


Figure 14. Gate Charge Waveforms for Constant Gate Current

Test Circuits and Waveforms

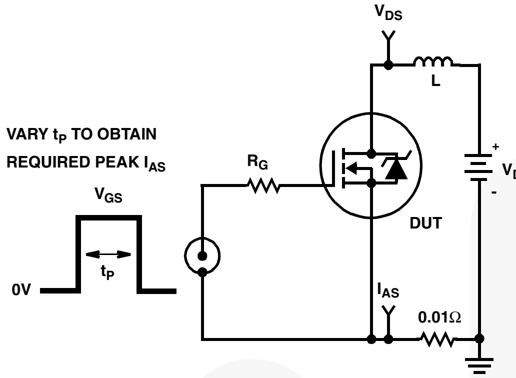


Figure 15. Unclamped Energy Test Circuit

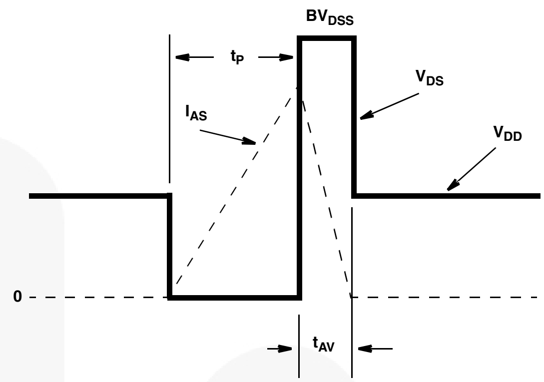


Figure 16. Unclamped Energy Waveforms

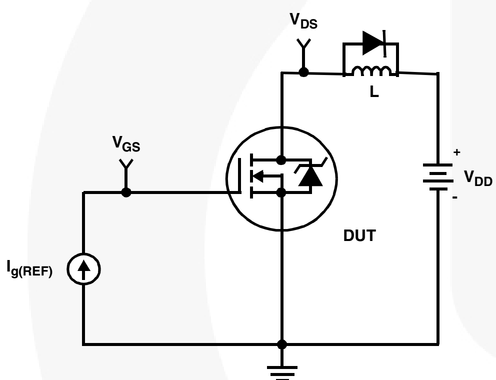


Figure 17. Gate Charge Test Circuit

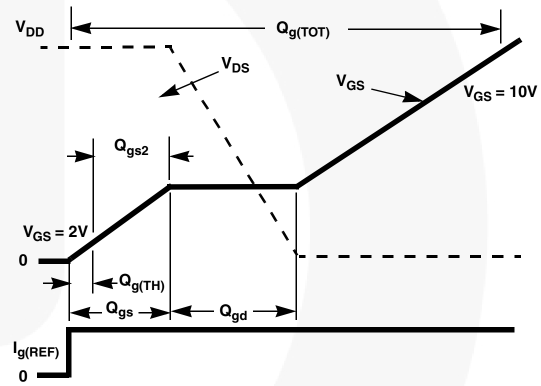


Figure 18. Gate Charge Waveforms

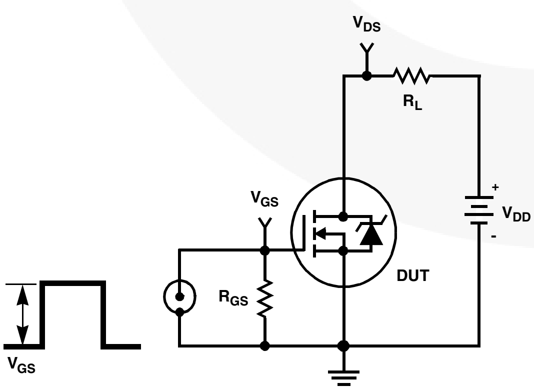


Figure 19. Switching Time Test Circuit

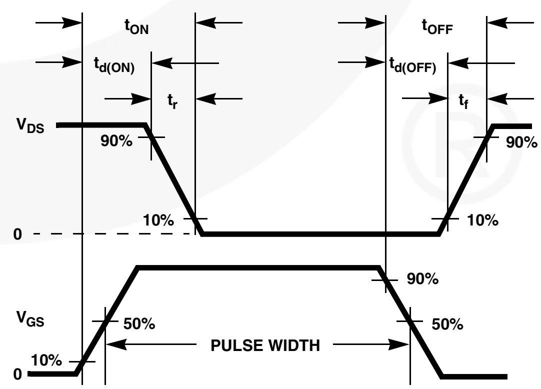
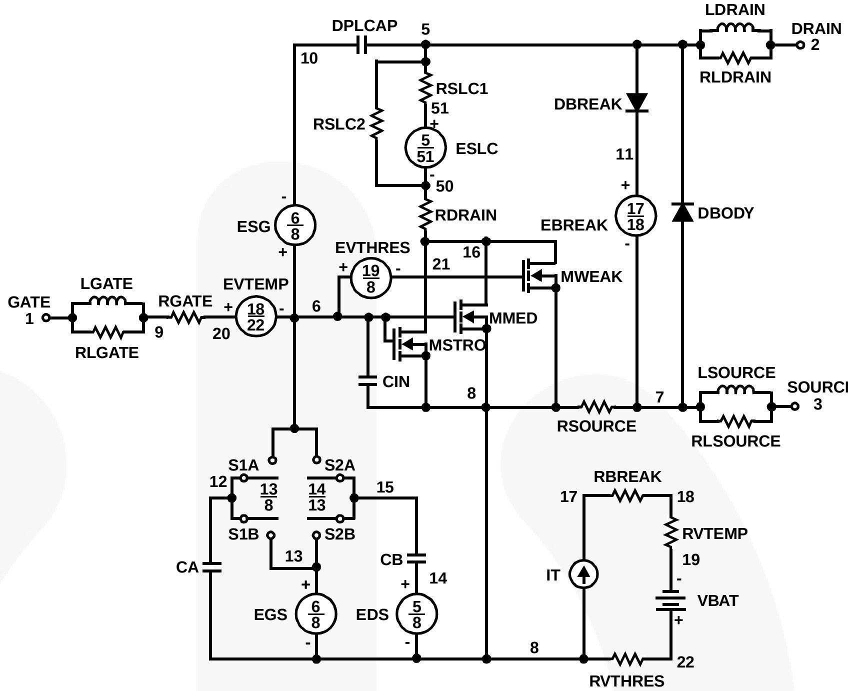


Figure 20. Switching Time Waveforms

PSPICE Electrical Model

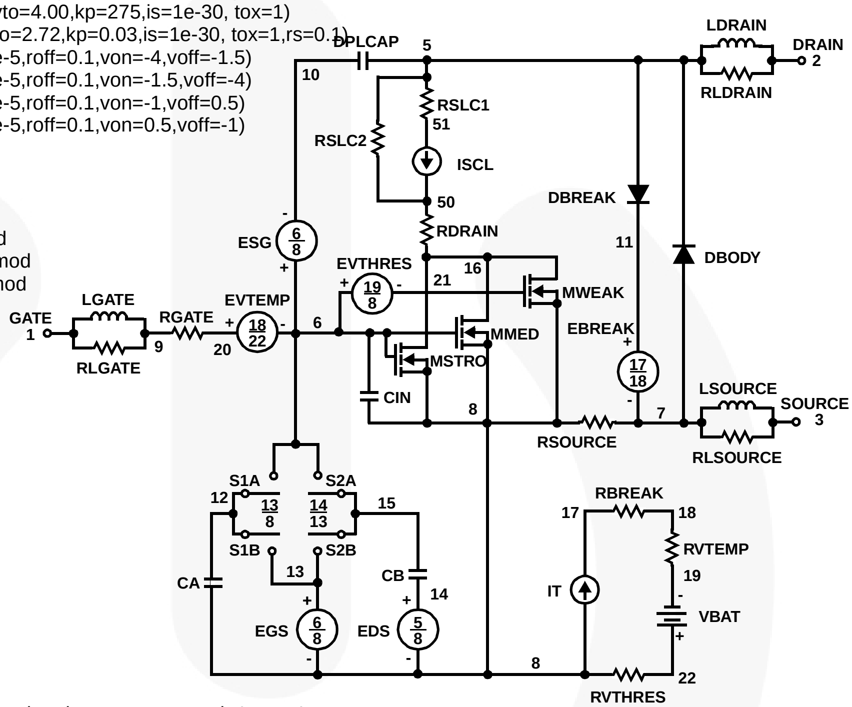



```
.SUBCKT FDP038AN06A0  2 1 3 ; rev July 04, 2002
Ca 12 8 1.5e-9
Cb 15 14 1.5e-9
Cin 6 8 6.1e-9

Dbody 7 5 DbodyMOD
Dbreak 5 11 DbreakMOD
Dplcap 10 5 DplcapMOD

Ebreak 11 7 17 18 69.3
Eds 14 8 5 8 1
Egs 13 8 6 8 1
Esg 6 10 6 8 1
Evthres 6 21 19 8 1
Evtemp 20 6 18 22 1

It 8 17 1

Lgate 1 9 4.81e-9
Ldrain 2 5 1.0e-9
Lsource 3 7 4.63e-9

RLgate 1 9 48.1
RLdrain 2 5 10
RLsource 3 7 46.3

Mmed 16 6 8 8 MmedMOD
Mstro 16 6 8 8 MstroMOD
Mweak 16 21 8 8 MweakMOD

Rbreak 17 18 RbreakMOD 1
Rdrain 50 16 RdrainMOD 1e-4
Rgate 9 20 1.36
RSLC1 5 51 RSLCMOD 1e-6
RSLC2 5 50 1e3
Rsource 8 7 RsourceMOD 2.8e-3
Rvthres 22 8 RvthresMOD 1
Rvtemp 18 19 RvtempMOD 1
S1a 6 12 13 8 S1AMOD
S1b 13 12 13 8 S1BMOD
S2a 6 15 14 13 S2AMOD
S2b 13 15 14 13 S2BMOD

Vbat 22 19 DC 1

ESLC 51 50  VALUE={(V(5,51)/ABS(V(5,51)))*(PWR(V(5,51)/(1e-6*250),10))}

.MODEL DbodyMOD D (IS=2.4E-11 N=1.04 RS=1.65e-3 TRS1=2.7e-3 TRS2=2e-7
+ CJO=4.35e-9 M=5.4e-1 TT=1e-9 XTI=3.9)
.MODEL DbreakMOD D (RS=1.5e-1 TRS1=1e-3 TRS2=-8.9e-6)
.MODEL DplcapMOD D (CJO=1.7e-9 IS=1e-30 N=10 M=0.47)

.MODEL MmedMOD NMOS (VTO=3.3 KP=9 IS=1e-30 N=10 TOX=1 L=1u W=1u RG=1.36 T_abs=25)
.MODEL MstroMOD NMOS (VTO=4.00 KP=275 IS=1e-30 N=10 TOX=1 L=1u W=1u T_abs=25)
.MODEL MweakMOD NMOS (VTO=2.72 KP=0.03 IS=1e-30 N=10 TOX=1 L=1u W=1u RG=13.6 RS=0.1 T_abs=25)

.MODEL RbreakMOD RES (TC1=9e-4 TC2=-9e-7)
.MODEL RdrainMOD RES (TC1=4e-2 TC2=3e-4)
.MODEL RSLCMOD RES (TC1=1e-3 TC2=1e-5)
.MODEL RsourceMOD RES (TC1=5e-3 TC2=1e-6)
.MODEL RvthresMOD RES (TC1=-6.7e-3 TC2=-1.5e-5)
.MODEL RvtempMOD RES (TC1=-2.5e-3 TC2=1e-6)

.MODEL S1AMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-4 VOFF=-1.5)
.MODEL S1BMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-1.5 VOFF=-4)
.MODEL S2AMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=-1 VOFF=0.5)
.MODEL S2BMOD VSWITCH (RON=1e-5 ROFF=0.1 VON=0.5 VOFF=-1)
.ENDS
```

Note: For further discussion of the PSPICE model, consult **A New PSPICE Sub-Circuit for the Power MOSFET Featuring Global Temperature Options**; IEEE Power Electronics Specialist Conference Records, 1991, written by William J. Hepp and C. Frank Wheatley.

SABER Electrical Model

```
rev July 4, 2002
template FDP038AN06A0 n2,n1,n3 = m_temp
electrical n2,n1,n3
number m_temp=25
{
var i iscl
dp..model dbodymod =  (isl=2.4e-11,nl=1.04,rs=1.65e-3,trs1=2.7e-3,trs2=2e-7,cjo=4.35e-9,m=5.4e-1,tt=1e-9,xti=3.9)
dp..model dbreakmod = (rs=1.5e-1,trs1=1e-3,trs2=-8.9e-6)
dp..model dplcapmod =  (cjo=1.7e-9,isl=10e-30,nl=10,m=0.47)
m..model mmedmod = (type=_n,vto=3.3,kp=9,is=1e-30, tox=1)
m..model mstrongmod = (type=_n,vto=4.00,kp=275,is=1e-30, tox=1)
m..model mweakmod = (type=_n,vto=2.72,kp=0.03,is=1e-30, tox=1,rs=0.1)
sw_vcsp..model s1amod =  (ron=1e-5,roff=0.1,von=-4,voff=-1.5)
sw_vcsp..model s1bmod =  (ron=1e-5,roff=0.1,von=-1.5,voff=-4)
sw_vcsp..model s2amod =  (ron=1e-5,roff=0.1,von=-1,voff=0.5)
sw_vcsp..model s2bmod =  (ron=1e-5,roff=0.1,von=0.5,voff=-1)
c.ca n12 n8 = 1.5e-9
c.cb n15 n14 = 1.5e-9
c.cin n6 n8 = 6.1e-9

dp.dbody n7 n5 = model=dbodymod
dp.dbreak n5 n11 = model=dbreakmod
dp.dplcap n10 n5 = model=dplcapmod

spe.ebreak n11 n7 n17 n18 = 69.3
spe.eds n14 n8 n5 n8 = 1
spe.egs n13 n8 n6 n8 = 1
spe.esg n6 n10 n6 n8 = 1
spe.evthres n6 n21 n19 n8 = 1
spe.evtemp n20 n6 n18 n22 = 1

i.it n8 n17 = 1

l.lgate n1 n9 = 4.81e-9
l.ldrain n2 n5 = 1.0e-9
l.lsource n3 n7 = 4.63e-9

res.rlgate n1 n9 = 48.1
res.rldrain n2 n5 = 10
res.rlsource n3 n7 = 46.3

m.mmed n16 n6 n8 n8 = model=mmedmod, temp=m_temp, l=1u, w=1u
m.mstrong n16 n6 n8 n8 = model=mstrongmod, temp=m_temp, l=1u, w=1u
m.mweak n16 n21 n8 n8 = model=mweakmod, temp=m_temp, l=1u, w=1u

res.rbreak n17 n18  = 1, tc1=9e-4,tc2=-9e-7
res.rdrain n50 n16  = 1e-4, tc1=4e-2,tc2=3e-4
res.rgate n9 n20 = 1.36
res.rslc1 n5 n51  = 1e-6, tc1=1e-3,tc2=1e-5
res.rslc2 n5 n50 = 1e3
res.rsource n8 n7  = 2.8e-3, tc1=5e-3,tc2=1e-6
res.rvthres n22 n8  = 1, tc1=-6.7e-3,tc2=-1.5e-5
res.rvtemp n18 n19  = 1, tc1=-2.5e-3,tc2=1e-6
sw_vcsp.s1a n6 n12 n13 n8 = model=s1amod
sw_vcsp.s1b n13 n12 n13 n8 = model=s1bmod
sw_vcsp.s2a n6 n15 n14 n13 = model=s2amod
sw_vcsp.s2b n13 n15 n14 n13 = model=s2bmod

v.vbat n22 n19 = dc=1
equations {
i (n51->n50) +=iscl
iscl: v(n51,n50) = ((v(n5,n51)/(1e-9+abs(v(n5,n51))))*((abs(v(n5,n51)*1e6/250))** 10))
}
```



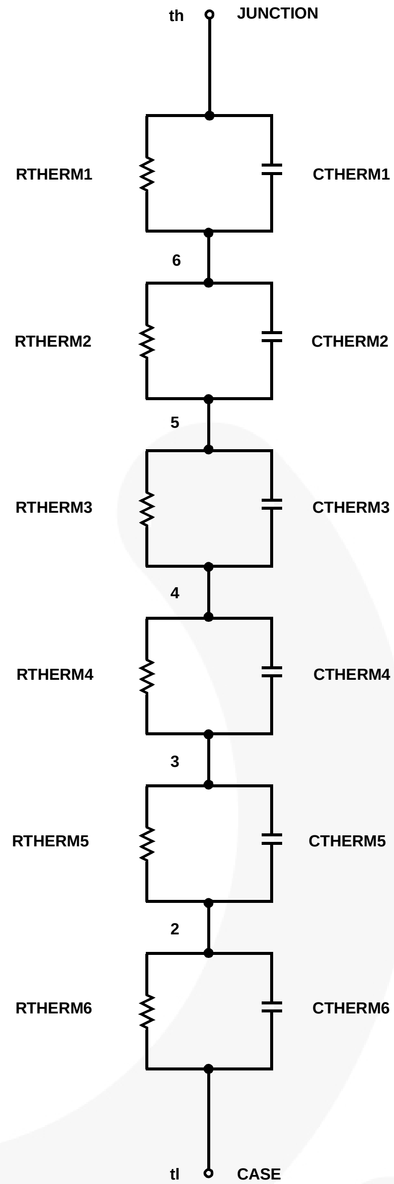
SPICE Thermal Model

REV 23 July 4, 2002

FDP038AN06A0T

CTHERM1 TH 6 6.45e-3
CTHERM2 6 5 3e-2
CTHERM3 5 4 1.4e-2
CTHERM4 4 3 1.65e-2
CTHERM5 3 2 4.85e-2
CTHERM6 2 TL 1e-1

RTHERM1 TH 6 3.24e-3
RTHERM2 6 5 8.08e-3
RTHERM3 5 4 2.28e-2
RTHERM4 4 3 1e-1
RTHERM5 3 2 1.1e-1
RTHERM6 2 TL 1.4e-1



SABER Thermal Model

SABER thermal model FDP035AN06A0T
template thermal_model th tl
thermal_c th, tl
{
ctherm.ctherm1 th 6 =6.45e-3
ctherm.ctherm2 6 5 =3e-2
ctherm.ctherm3 5 4 =1.4e-2
ctherm.ctherm4 4 3 =1.65e-2
ctherm.ctherm5 3 2 =4.85e-2
ctherm.ctherm6 2 tl =1e-1

rtherm.rtherm1 th 6 =3.24e-3
rtherm.rtherm2 6 5 =8.08e-3
rtherm.rtherm3 5 4 =2.28e-2
rtherm.rtherm4 4 3 =1e-1
rtherm.rtherm5 3 2 =1.1e-1
rtherm.rtherm6 2 tl=1.4e-1
}

Mechanical Dimensions

TO-220 3L

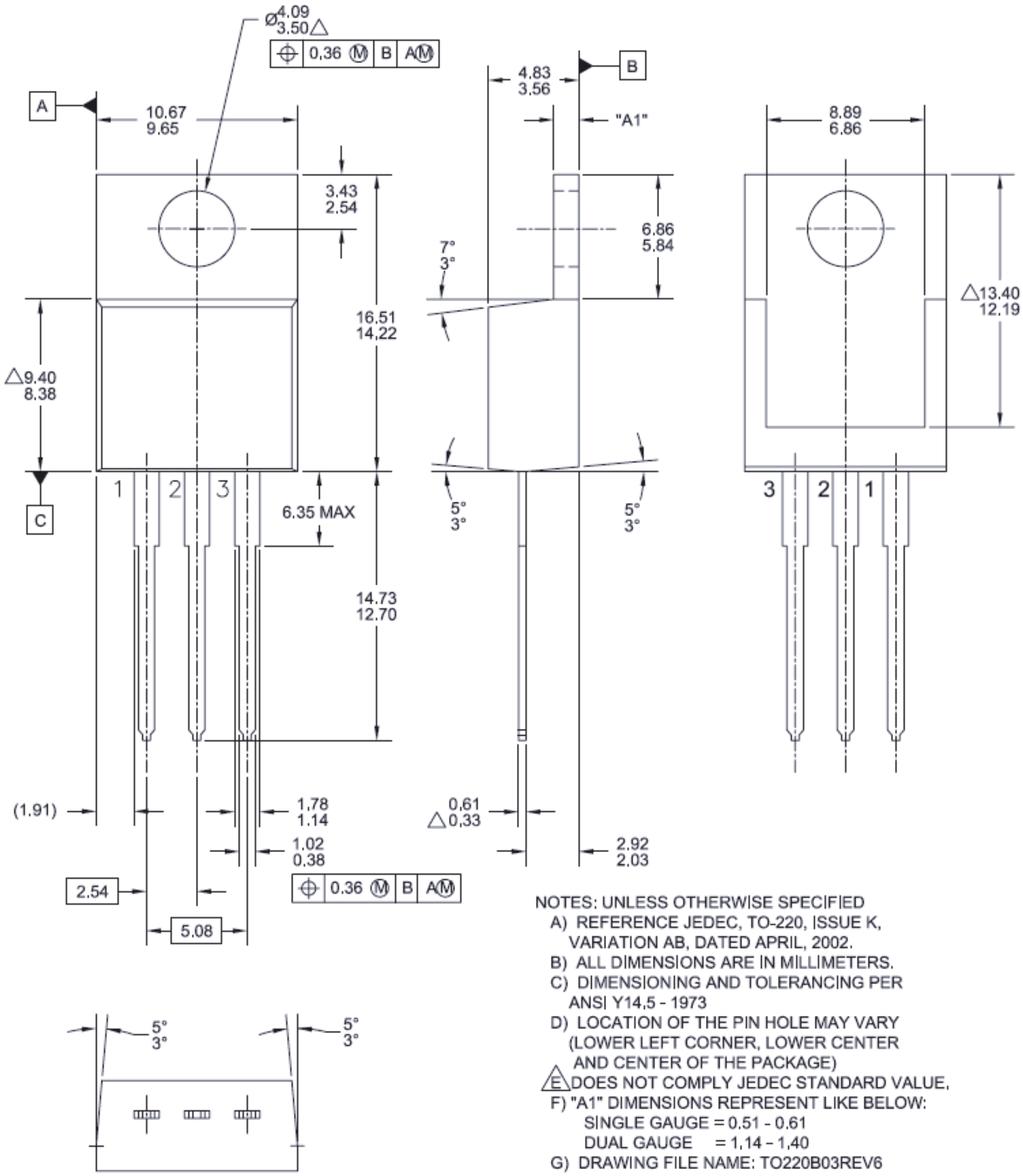


Figure 21. TO-220, Molded, 3Lead, Jedec Variation AB

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT220-003

Dimension in Millimeters

Mechanical Dimensions

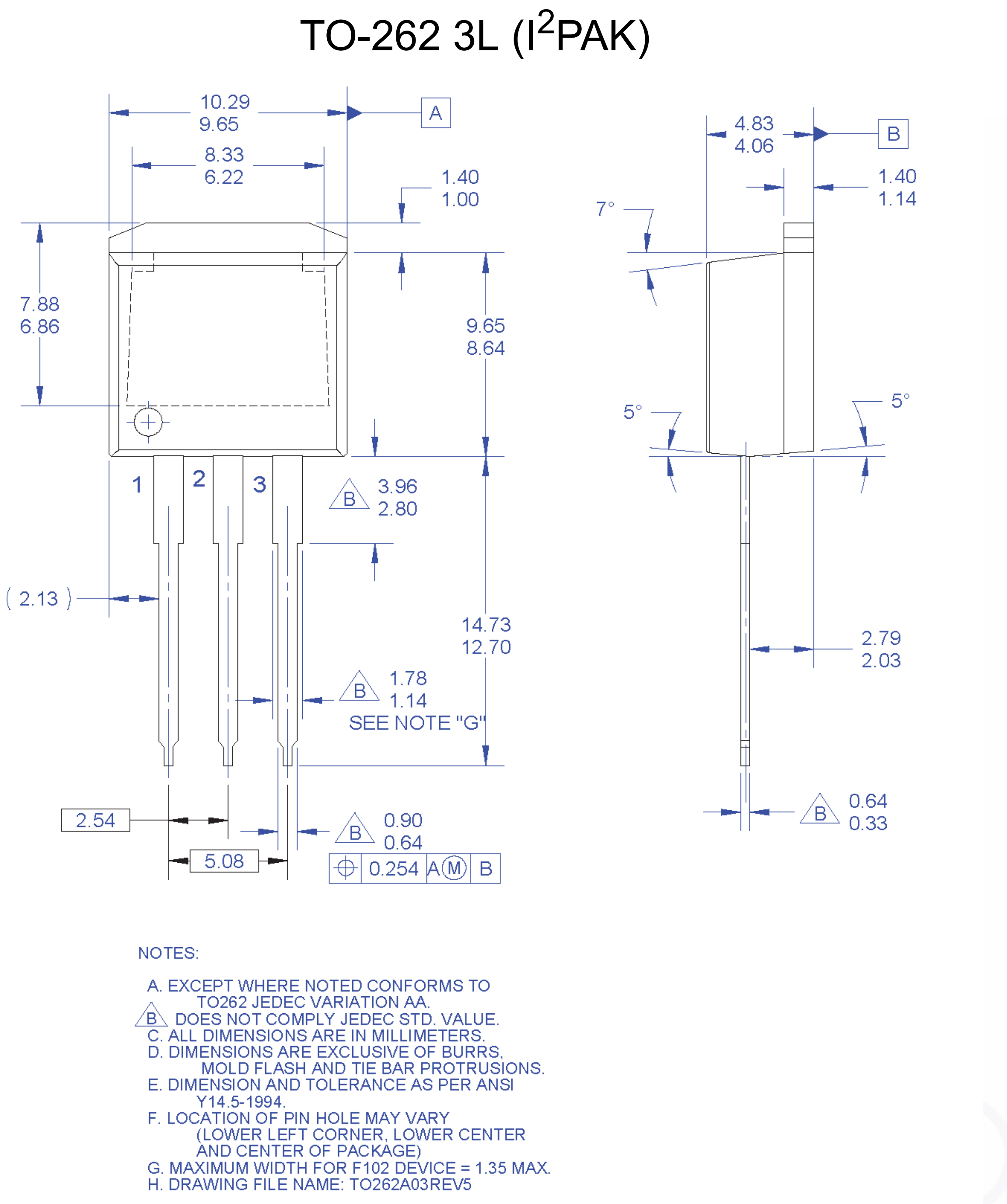


Figure 22. 3LD, TO262, Jedec Variation AA (I²PAK)

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Dimension in Millimeters

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